

SANYO	No.5267	<h1 style="margin: 0;">2SJ417</h1> <p style="margin: 0;">P-Channel Silicon MOSFET</p> <h2 style="margin: 0;">Ultrahigh-Speed Switching Applications</h2>
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Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Absolute Maximum Ratings at Ta = 25°C

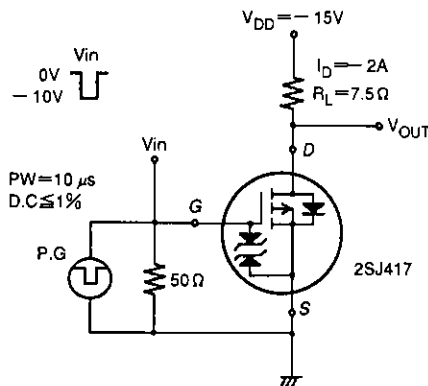
Drain-to-Source Voltage	V_{DSS}	-30	V	unit
Gate-to-Source Voltage	V_{GSS}	±20	V	
Drain Current(DC)	I_D	-4	A	
Drain Current(Pulse)	I_{DP}	-16	A	
Allowable Power Dissipation	P_D	1	W	
		$T_c = 25^\circ\text{C}$		
Channel Temperature	T_{ch}	20	W	
Storage Temperature	T_{stg}	150	°C	
		-55 to +150	°C	

Electrical Characteristics at Ta = 25°C

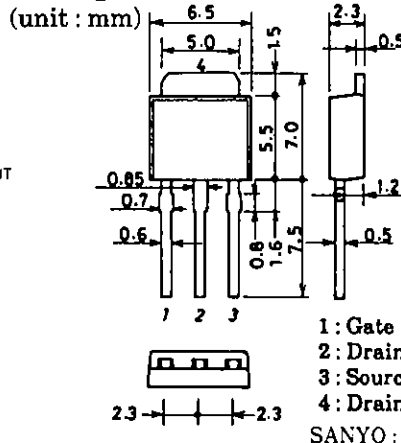
			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}, V_{GS} = 0$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{V}, V_{GS} = 0$			-100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16\text{V}, V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}, I_D = -1\text{mA}$	-1.0		-2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10\text{V}, I_D = -2\text{A}$	2	4		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$I_D = -2\text{A}, V_{GS} = -10\text{V}$		120	160	mΩ
	$R_{DS(on)}$	$I_D = -2\text{A}, V_{GS} = -4\text{V}$		210	290	mΩ
Input Capacitance	C_{iss}	$V_{DS} = -10\text{V}, f = 1\text{MHz}$		370		pF
Output Capacitance	C_{oss}	$V_{DS} = -10\text{V}, f = 1\text{MHz}$		230		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -10\text{V}, f = 1\text{MHz}$		70		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		10		ns
Rise Time	t_r	"		50		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		135		ns
Fall Time	t_f	"		125		ns
Diode Forward Voltage	V_{SD}	$I_S = -4\text{A}, V_{GS} = 0$	-1.0	-1.2		V

Marking : JJ

Switching Time Test Circuit

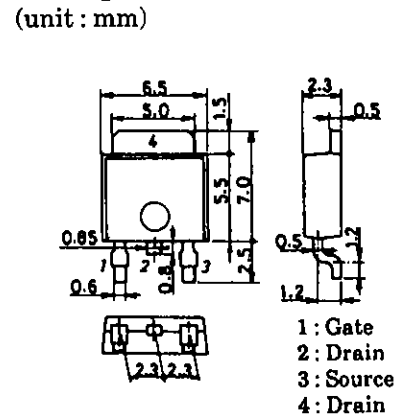


Package Dimensions 2083B



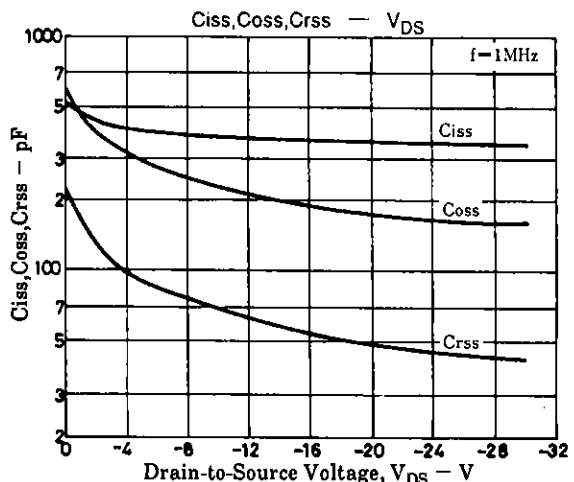
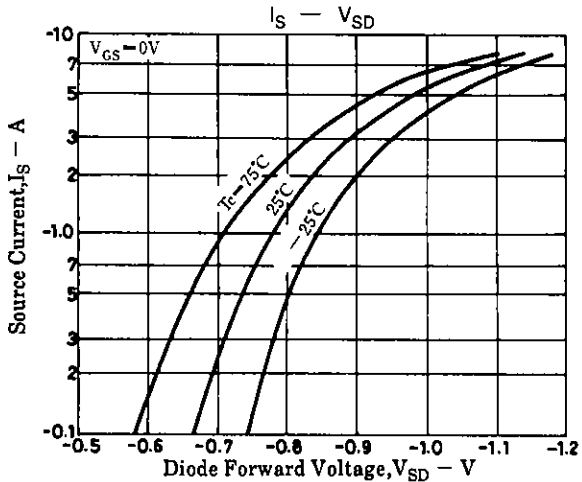
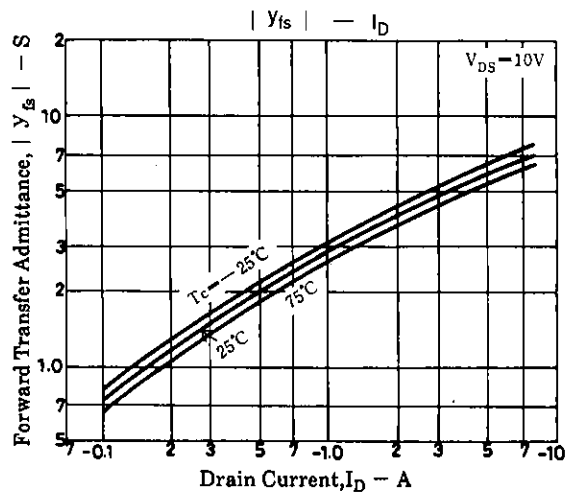
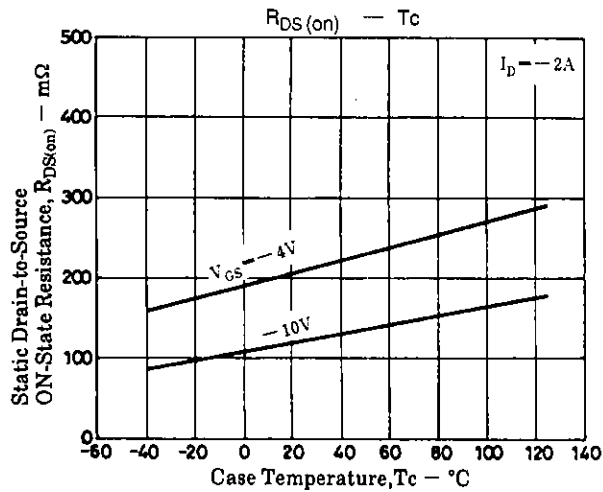
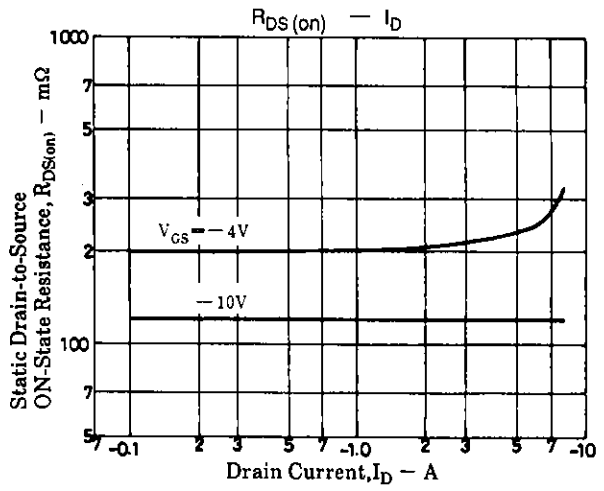
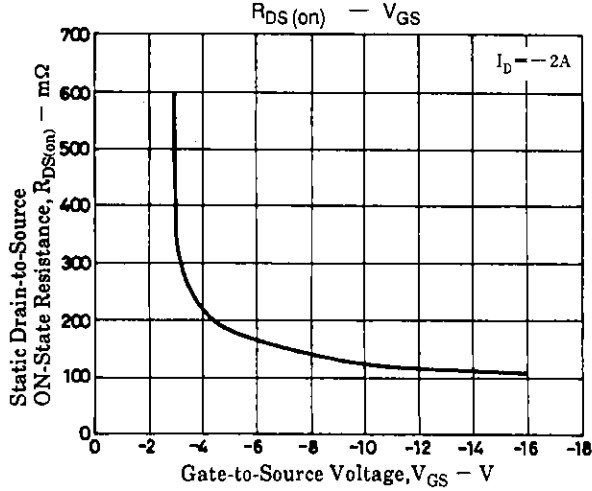
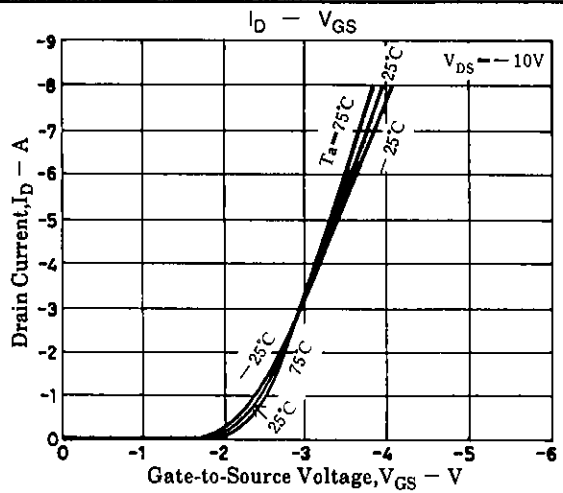
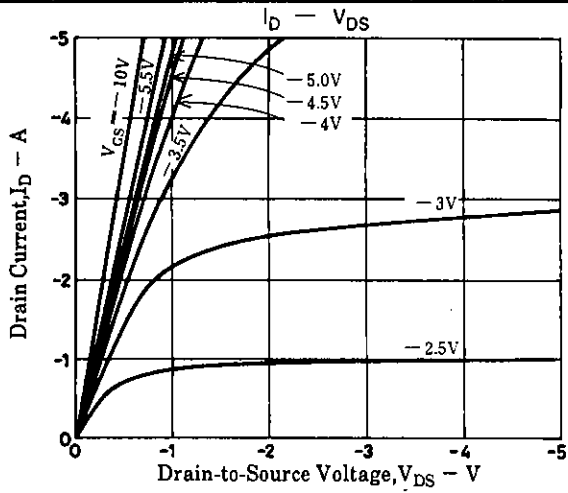
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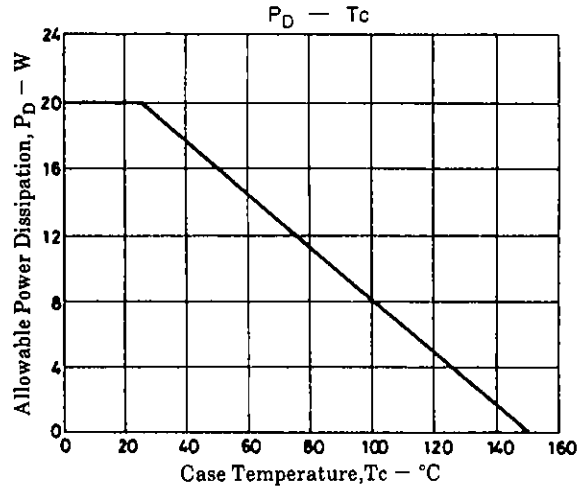
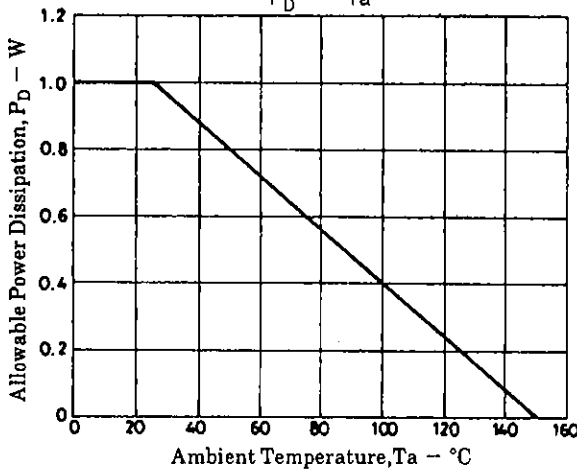
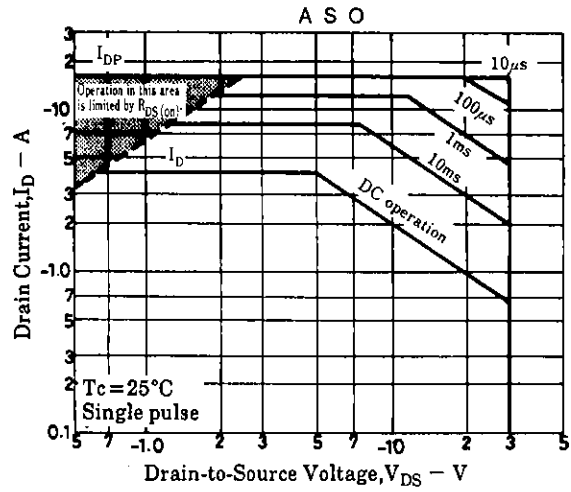
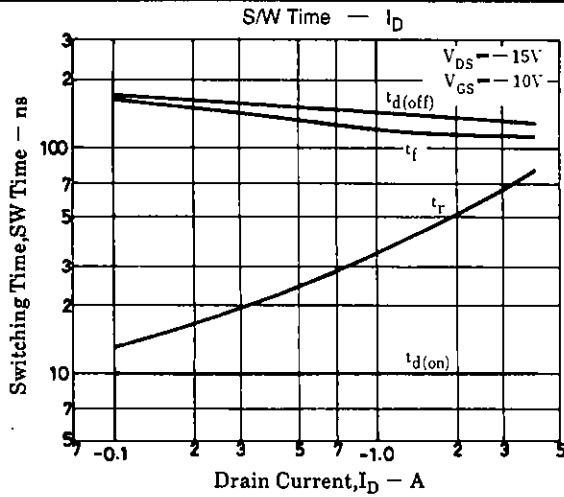
Package Dimensions 2092B



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